(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property Organization
International Bureau

(43) International Publication Date
6 November 2008 (06.11.2008)

PCT

(10) International Publication Number
WO 2008/132569 A1

(51) International Patent Classification:
H01L 21/762 (2006.01) *H01L 21/324* (2006.01)
H01L 21/20 (2006.01)

(21) International Application Number:
PCT/IB2008/000967

(22) International Filing Date: 15 April 2008 (15.04.2008)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
FR0754777 27 April 2007 (27.04.2007) FR

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(81) Designated States *(unless otherwise indicated, for every kind of national protection available)*: AE, AG, AL, AM, AO, AT, AU, AZ, BA, BB, BG, BH, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DO, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, GT, HN, HR, HU, ID, IL, IN, IS, JP, KE, KG, KM, KN, KP, KR, KZ, LA, LC, LK, LR, LS, LT, LU, LY, MA, MD, ME, MG, MK, MN, MW, MX, MY, MZ, NA, NG, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RS, RU, SC, SD, SE, SG, SK, SL, SM, SV, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, ZA, ZM, ZW.

(84) Designated States *(unless otherwise indicated, for every kind of regional protection available)*: ARIPO (BW, GH, GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HR, HU, IE, IS, IT, LT, LU, LV, MC, MT, NL,

[Continued on next page]

(54) Title: METHOD FOR TRANSFERRING AN EPITAXIAL LAYER

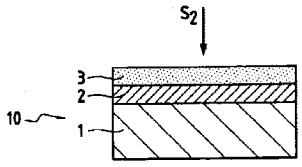


FIG.1B

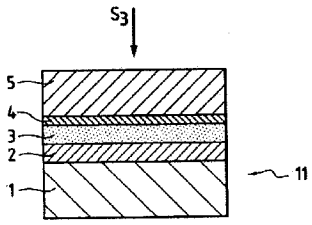


FIG.1C

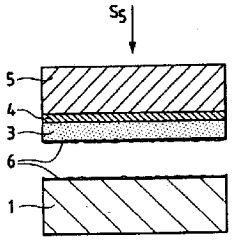


FIG.1D

(57) Abstract: A method for producing an epitaxial layer (3) comprising: a fabrication step of a structure (10) comprising: formation of an intermediate layer (2) on a donor substrate (1); and formation (S2) of the epitaxial layer (3) on the intermediate layer (2) by epitaxy; the melting temperature of the intermediate layer (2) being lower than the melting temperature of the epitaxial layer (3); and a detachment step (S5) of the epitaxial layer (3) from the donor substrate (1) by applying at least one thermal treatment, said thermal treatment being performed at a temperature comprised between the melting temperature of the intermediate layer (2) and the melting temperature of the epitaxial layer (3).

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NO, PL, PT, RO, SE, SI, SK, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

Declaration under Rule 4.17:

— *of inventorship (Rule 4.17(iv))*

Published:

— *with international search report*